











CSD17483F4

SLPS447D - JULY 2013-REVISED DECEMBER 2016

CSD17483F4 30-V N-Channel FemtoFET™ MOSFET

Features

- Low On Resistance
- Low Q_g and Q_{gd}
- Low-Threshold Voltage
- Ultra-Small Footprint (0402 Case Size)
 - 1.0 mm × 0.6 mm
- Ultra-Low Profile
 - 0.35-mm Height
- Integrated ESD Protection Diode
 - Rated > 4-kV HBM
 - Rated > 2-kV CDM
- Lead and Halogen Free
- **RoHS Compliant**

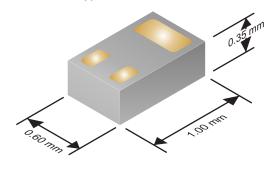
2 Applications

- Optimized for Load Switch Applications
- Optimized for General Purpose Switching **Applications**
- Single-Cell Battery Applications
- Handheld and Mobile Applications

3 Description

FemtoFET™ This 200-mΩ, 30-V N-Channel MOSFET technology is designed and optimized to minimize the footprint in many handheld and mobile applications. This technology is capable of replacing standard small signal MOSFETs while providing at least a 60% reduction in footprint size.

Typical Part Dimensions



Product Summary

T _A = 25°	°C	TYPICAL VA	UNIT	
V_{DS}	Drain-to-Source Voltage	30		>
Q_g	Gate Charge Total (4.5 V)	1010		рС
Q_{gd}	Gate Charge Gate-to-Drain	Charge Gate-to-Drain 130		
		V _{GS} = 1.8 V	370	
R _{DS(on)}	Drain-to-Source On Resistance	V _{GS} = 2.5 V	240	mΩ
		V _{GS} = 4.5 V 200		
V _{GS(th)}	Threshold Voltage	0.85		V

Device Information⁽¹⁾

DEVICE	QTY	MEDIA	PACKAGE	SHIP
CSD17483F4	3000		Femto(0402)	Tape
CSD17483F4T	250	7-Inch Reel	1.00 mm × 0.60 mm SMD Lead Less	and Reel

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Absolute Maximum Ratings

		-		
T _A = 25	°C unless otherwise stated	VALUE	UNIT	
V_{DS}	Drain-to-Source Voltage	30	V	
V_{GS}	Gate-to-Source Voltage	12	V	
I_D	Continuous Drain Current, T _A = 25°C ⁽¹⁾	1.5	Α	
I_{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	5	Α	
	Continuous Gate Clamp Current	35	mA	
I_{G}	Pulsed Gate Clamp Current ⁽²⁾	350	IIIA	
P_D	Power Dissipation ⁽¹⁾	500	mW	
\/	Human-Body Model (HBM)	4	kV	
$V_{(ESD)}$	Charged-Device Model (CDM)	2	KV	
T _J , T _{stg}	Operating Junction, Storage Temperature	-55 to 150	°C	
E _{AS}	Avalanche Energy, Single Pulse I_D = 7.4 A, L = 0.1 mH, R_G = 25 Ω	2.7	mJ	

- (1) Typical $R_{\theta JA} = 90^{\circ}\text{C/W}$ on $1-\text{in}^2$ (6.45-cm²), (0.071-mm) thick Cu pad on a 0.06-in (1.52-mm) thick FR4
- (2) Pulse duration \leq 300 μ s, duty cycle \leq 2%.

Top View

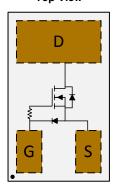




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4 Revision History

Cł	hanges from Revision C (September 2014) to Revision D	Page
•	Added Receiving Notification of Documentation Updates in the Device and Documentation Support section	<mark>7</mark>
•	Added Community Resources in the Device and Documentation Support section	<mark>7</mark>
•	Updated all mechanical drawings, increased the size of the pads in the Recommended Stencil Pattern section	8
C I	hanges from Revision B (January 2014) to Revision C	Page
CI	- Contract to the contract of	гауе
•	Corrected timing V _{DS} to read 15 V	3
Cł	hanges from Revision A (November 2013) to Revision B	Page
•	Added I _G parameter	1
•	Lowered I _{DSS} limit	
•	Lowered I _{GSS} limit	3
Cł	hanges from Original (July 2013) to Revision A	Page
	Removed jumbo reel info and included small reel info	 1

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5 Specifications

5.1 Electrical Characteristics

 $T_A = 25^{\circ}C$ (unless otherwise stated)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC	CHARACTERISTICS					
BV _{DSS}	Drain-to-source voltage	$V_{GS} = 0 \text{ V}, I_{DS} = 250 \mu\text{A}$	30			V
I _{DSS}	Drain-to-source leakage current	V _{GS} = 0 V, V _{DS} = 9.6 V			100	nA
I _{GSS}	Gate-to-source leakage current	V _{DS} = 0 V, V _{GS} = 4 V			50	nA
V _{GS(th)}	Gate-to-source threshold voltage	$V_{DS} = V_{GS}, I_{DS} = 250 \mu A$	0.65	0.85	1.10	V
		V _{GS} = 1.8 V, I _{DS} =0.5 A		370	550	
Б	Dunin to anyone an anniatana	V _{GS} = 2.5 V, I _{DS} =0.5 A		240	310	0
R _{DS(on)}	Drain-to-source on resistance	V _{GS} = 4.5 V, I _{DS} = 0.5 A		200	260	mΩ
		V _{GS} = 8 V, I _{DS} =0.5 A		185	240	
9 _{fs}	Transconductance	V _{DS} = 15 V, I _{DS} = 0.5 A		2.4		S
DYNAMI	C CHARACTERISTICS					
C _{iss}	Input capacitance			145	190	pF
C _{oss}	Output capacitance	$V_{GS} = 0 \text{ V}, V_{DS} = 15 \text{ V},$ f = 1 MHz		42	55	pF
C _{rss}	Reverse transfer capacitance	J = 1 WI 12		2	3	pF
R _G	Series gate resistance			23		Ω
Q _q	Gate charge total (4.5 V)			1010	1300	рС
Q_{gd}	Gate charge gate-to-drain	V 45.V 1 0.5.A		130		рС
Q _{gs}	Gate charge gate-to-source	V _{DS} = 15 V, I _{DS} = 0.5 A		220		рС
Q _{g(th)}	Gate charge at V _{th}			145		рС
Q _{oss}	Output charge	V _{DS} = 15 V, V _{GS} = 0 V		1095		рС
t _{d(on)}	Turnon delay time			3.3		ns
t _r	Rise time	V _{DS} = 15 V, V _{GS} = 4.5 V,		1.3		ns
t _{d(off)}	Turnoff delay time	$I_{DS} = 0.5 \text{ A}, R_G = 2 \Omega$ 10.6			ns	
t _f	Fall time			3.4		ns
DIODE C	CHARACTERISTICS				1	
V _{SD}	Diode forward voltage	I _{SD} = 0.5 A, V _{GS} = 0 V		0.73	0.9	V
Q _{rr}	Reverse recovery charge			1475		рС
t _{rr}	Reverse recovery time	V_{DS} = 15 V, I_F = 0.5 A, di/dt = 300 A/ μ s		5.5		ns

5.2 Thermal Information

 $T_A = 25$ °C (unless otherwise stated)

	THERMAL METRIC	TYPICAL VALUES	UNIT
D	Junction-to-ambient thermal resistance ⁽¹⁾	90	°C/W
$\kappa_{\theta JA}$	Junction-to-ambient thermal resistance ⁽²⁾	250	C/VV

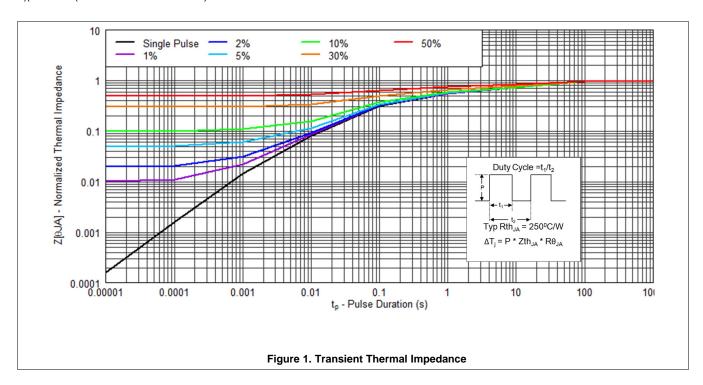
 ⁽¹⁾ Device mounted on FR4 material with 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu.
 (2) Device mounted on FR4 material with minimum Cu mounting area.

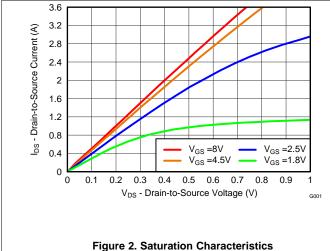
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5.3 Typical MOSFET Characteristics

 $T_A = 25$ °C (unless otherwise stated)





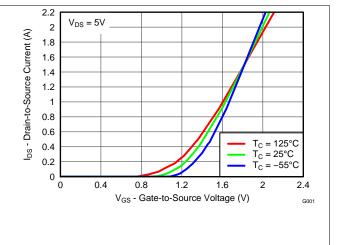
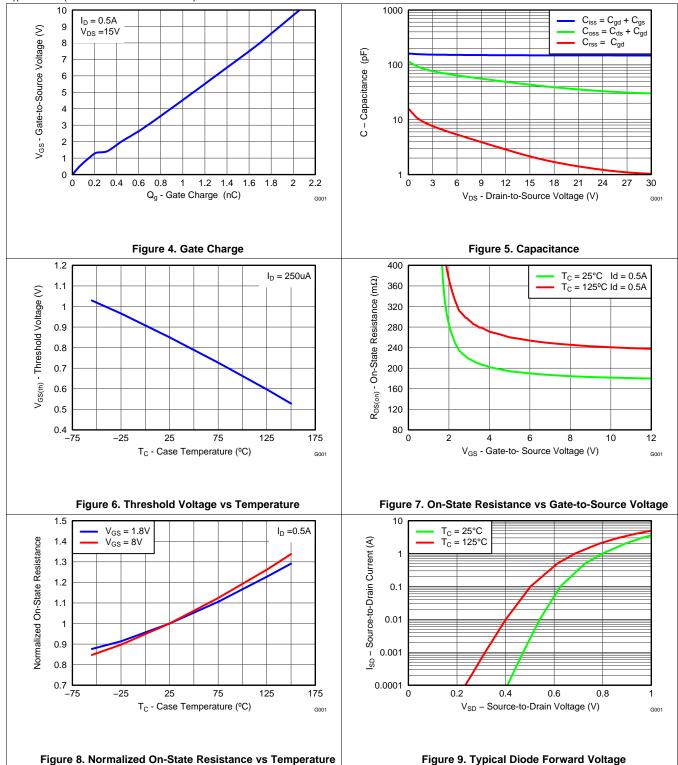


Figure 3. Transfer Characteristics



Typical MOSFET Characteristics (continued)

 $T_A = 25$ °C (unless otherwise stated)

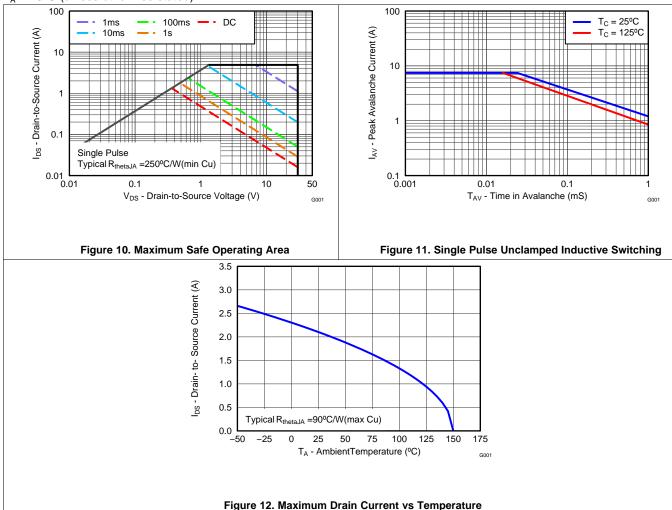


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Typical MOSFET Characteristics (continued)

 $T_A = 25$ °C (unless otherwise stated)





6 Device and Documentation Support

6.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

6.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

6.3 Trademarks

FemtoFET, E2E are trademarks of Texas Instruments.

All other trademarks are the property of their respective owners.

6.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.5 Glossary

SLYZ022 — TI Glossary.

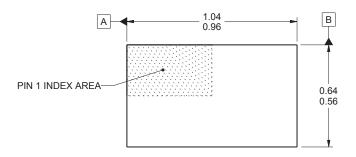
This glossary lists and explains terms, acronyms, and definitions.



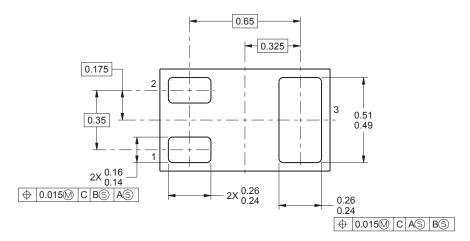
7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 Mechanical Dimensions



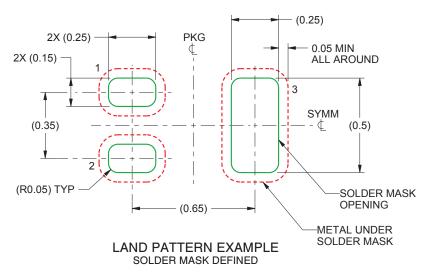




- (1) All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- (2) This drawing is subject to change without notice.
- (3) This package is a Pb-free bump design. Bump finish may vary. To determine the exact finish, refer to the device data sheet or contact a local TI representative.

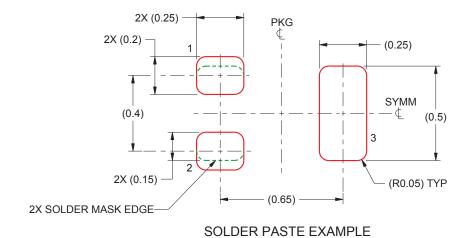


7.2 Recommended Minimum PCB Layout



- (1) All dimensions are in millimeters.
- (2) For more information, see QFN/SON PCB Attachment (SLUA271).

7.3 Recommended Stencil Pattern



- (1) All dimensions are in millimeters.
- (2) Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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PACKAGE OPTION ADDENDUM

7-Dec-2016

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
CSD17483F4	ACTIVE	PICOSTAR	YJC	3	3000	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	-55 to 150	DP	Samples
CSD17483F4T	ACTIVE	PICOSTAR	YJC	3	250	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	-55 to 150	DP	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

7-Dec-2016

n no event shall TI's liabili	ty arising out of such information	exceed the total purchase	price of the TI part(s)	at issue in this document sold by	TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

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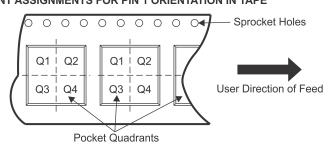
TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD17483F4	PICOST AR	YJC	3	3000	178.0	8.4	0.7	1.1	0.46	4.0	8.0	Q2
CSD17483F4	PICOST AR	YJC	3	3000	180.0	8.4	0.7	1.1	0.46	4.0	8.0	Q2
CSD17483F4T	PICOST AR	YJC	3	250	180.0	8.4	0.7	1.1	0.46	4.0	8.0	Q2
CSD17483F4T	PICOST AR	YJC	3	250	178.0	8.4	0.7	1.1	0.46	4.0	8.0	Q2

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*All dimensions are nominal

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Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD17483F4	PICOSTAR	YJC	3	3000	220.0	220.0	35.0
CSD17483F4	PICOSTAR	YJC	3	3000	182.0	182.0	20.0
CSD17483F4T	PICOSTAR	YJC	3	250	182.0	182.0	20.0
CSD17483F4T	PICOSTAR	YJC	3	250	220.0	220.0	35.0

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